Department of Materials Science and Engineering National Chiao Tung University

Taiwan, Republic of China

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We have carefully read the dissertation entitled

Material Characterizations and	Process Development of
WNx T-gate AlGaN/GaN H	
Transistor for High Temperature Applications	
submitted by Chao-YI Fang in partial fulfillment of the requirement of the degree of Doctor of Philosophy and	
recommend its acceptance.	OCTOR OF THEOGOTH AND
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